DIELECTRIC STACK

ABSTRACT

A method of forming a device is disclosed. The method includes providing a substrate and forming a device layer on the substrate having a formed thickness T_{FD}. A capping layer is formed on the substrate having a formed thickness T_{FC}. Forming the capping layer consumes a desired amount of the device layer to cause the thickness of the device layer to be about the target thickness T_{TD}. The thickness of the capping layer is adjusted from T_{FC} to about a target thickness T_{TC}.

Fig. 4